

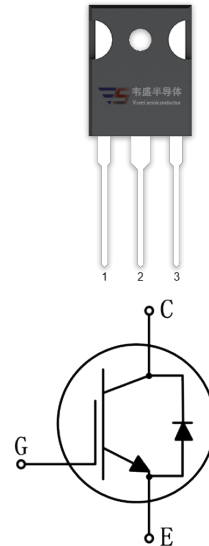
Key performance:

- $V_{CE}=1200V$
- $I_C=25A@T_C=100^{\circ}C$
- $V_{CE(sat)}=1.7V$

TO-247

Features:

- Trench and field-stop technology
- High speed switching
- Low collector to emitter saturation voltage
- Easy parallel switching capability
- Short circuit withstands time 10 μ s
- High ruggedness performance
- RoHS compliant



Applications:

- General inverter
- Motor drives

Package parameters

Type	Marking	Package	Packaging Method
VSG25N120-T7	VSG25N120	TO-247	Tube

Maximum ratings

Symbol	Parameter	Values	Unit
V_{CES}	Collector-emitter voltage	1200	V
V_{GES}	Gate-emitter voltage	± 20	V
I_C	Continuous collector current ($T_C=25^\circ\text{C}$)	50	A
	Continuous collector current ($T_C=100^\circ\text{C}$)	25	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	100	A
I_F	Diode continuous forward current ($T_C=100^\circ\text{C}$)	25	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	100	A
t_{sc}	Short circuit withstand time	10	μs
P_{tot}	Power dissipation ($T_C=25^\circ\text{C}$)	428	W
	Power dissipation ($T_C=100^\circ\text{C}$)	214	W
T_{vj}	Operating junction temperature range	-40 to +175	$^\circ\text{C}$
T_{stg}	Storage temperature range	-55 to +150	$^\circ\text{C}$

Thermal characteristics

Symbol	Parameter	Values		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	0.35	K/ W
$R_{th(j-c)}$	Thermal resistance, junction to case for Diode	-	0.90	K/ W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	-	40	K/ W

Electrical characteristics of IGBT ($T_{vj}=25^{\circ}\text{C}$ unless otherwise specified)

Static characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-emitterbreakdown voltage	$V_{GE}=0V, I_C=250\mu A$	1200	-	-	V
I_{CES}	Collector-emitter leakage current	$V_{CE}=1200V, V_{GE}=0V$	-	-	100	μA
I_{GES}	Gate leakage current, forward	$V_{GE}=20V, V_{CE}=0V$	-	-	100	nA
	Gate leakage current, reverse	$V_{GE}=-20V, V_{CE}=0V$	-	-	-100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	$V_{GE}=V_{CE}, I_C=1mA$	5.8	6.1	6.3	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE}=15V, I_C=25A$	-	1.7	-	V
		$V_{GE}=15V, I_C=25A, T_{vj}=175^{\circ}\text{C}$	-	2.3	-	V

Dynamic characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
C_{ies}	Input capacitance	$V_{CE}=30V$ $V_{GE}=0V$ $f=1MHz$	-	2080	-	pF
C_{oes}	Output capacitance		-	105	-	pF
C_{res}	Reverse transfer capacitance		-	20	-	pF
Q_g	Total gate charge	$V_{CC}=960V$ $V_{GE}=15V$ $I_C=25A$	-	133	-	nC

Switching characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $V_{GE}=0/15V$ $I_C=25A$ $R_G=10\Omega$ Inductive load	-	31	-	ns
t_r	Rise time		-	62	-	ns
$t_{d(off)}$	Turn-offdelay time		-	184	-	ns
t_f	Fall time		-	59	-	ns
E_{on}	Turn-on energy		-	2.0	-	mJ
E_{off}	Turn-off energy		-	0.9	-	mJ
E_{ts}	Total switching energy		-	2.9	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $V_{GE}=0/15V$ $I_C=25A$ $R_G=10\Omega$ Inductive load $T_{vj}=175^{\circ}C$	-	33	-	ns
t_r	Rise time		-	67	-	ns
$t_{d(off)}$	Turn-offdelay time		-	206	-	ns
t_f	Fall time		-	87	-	ns
E_{on}	Turn-on energy		-	3.1	-	mJ
E_{off}	Turn-offenergy		-	1.3	-	mJ
E_{ts}	Total switching energy		-	4.4	-	mJ

Electrical characteristics of Diode ($T_{vj}=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
V_F	Diode forward voltage	$I_F=25\text{A}$	-	2.0	-	V
		$I_F=25\text{A}, T_{vj}=175^{\circ}\text{C}$	-	1.6	-	V
t_{rr}	Diode reverse recovery time	$V_R=600\text{V}$ $I_F=25\text{A}$ $di_F/dt=-250\text{A}/\mu\text{s}$	-	309	-	ns
I_{rrm}	Diode peak reverse recovery current		-	7	-	A
Q_{rr}	Diode reverse recovery charge		-	1038	-	nC
t_{rr}	Diode reverse recovery time	$V_R=600\text{V}$ $I_F=25\text{A}$ $di_F/dt=-250\text{A}/\mu\text{s}$	-	480	-	ns
I_{rrm}	Diode peak reverse recovery current		-	11	-	A
Q_{rr}	Diode reverse recovery charge	$T_{vj}=175^{\circ}\text{C}$	-	3000	-	nC

Typical performance characteristics

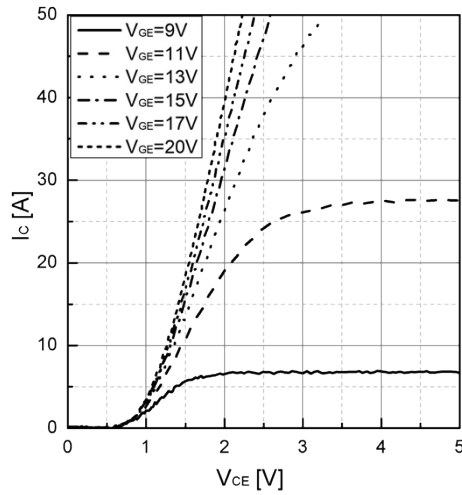


Fig 1. Typical output characteristic ($T_{vj}=25^{\circ}\text{C}$)

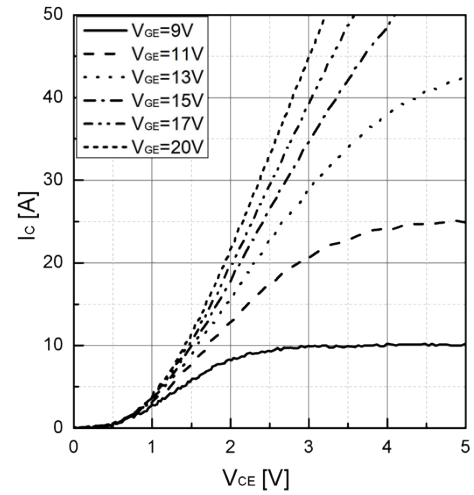


Fig 2. Typical output characteristic ($T_{vj}=175^{\circ}\text{C}$)

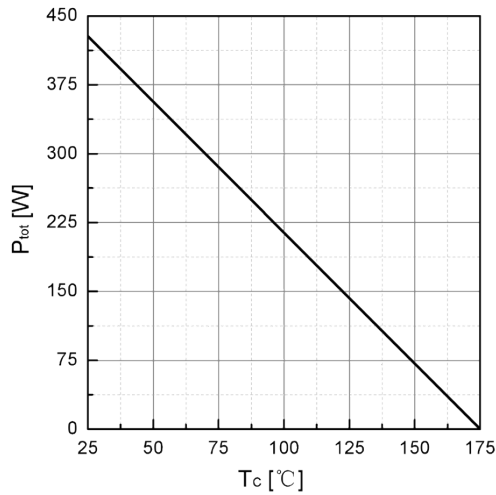


Fig 3. Power dissipation as a function of T_c

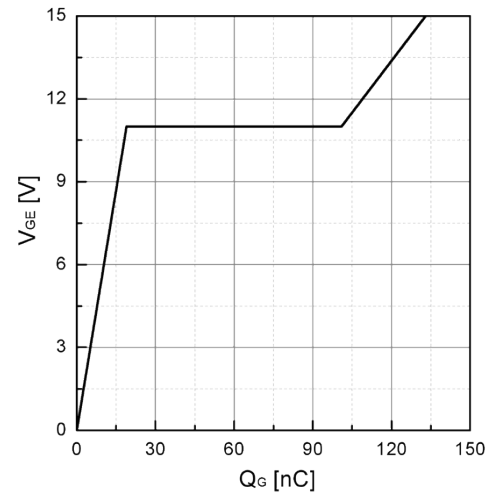


Fig 4. Typical Gate charge

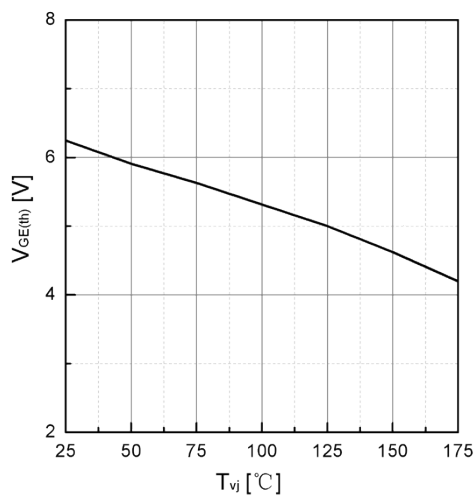


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj}
($I_c=1\text{mA}$)

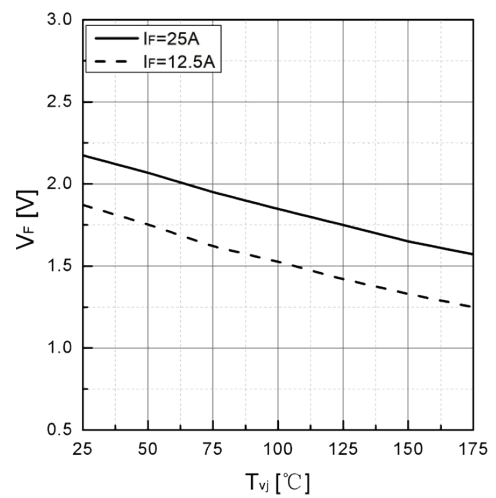


Fig 6. Typical V_F as a function of T_{vj}

Typical performance characteristics

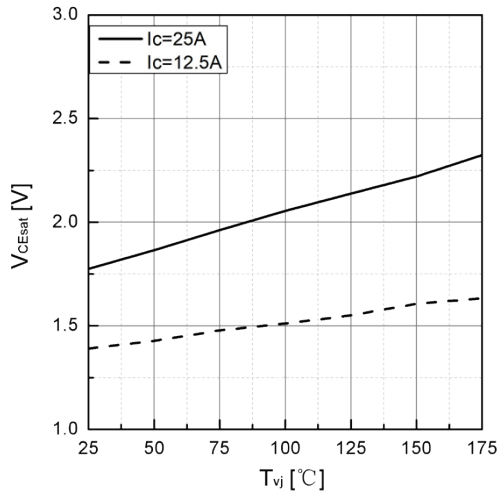


Fig 7. Typical V_{CEsat} as a function of T_{vj}

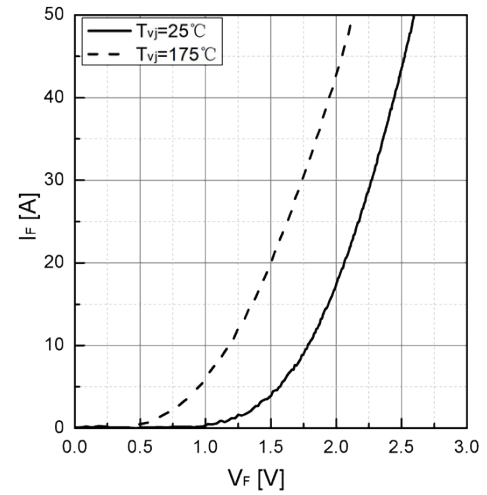


Fig 8. Typical I_F as a function of V_F

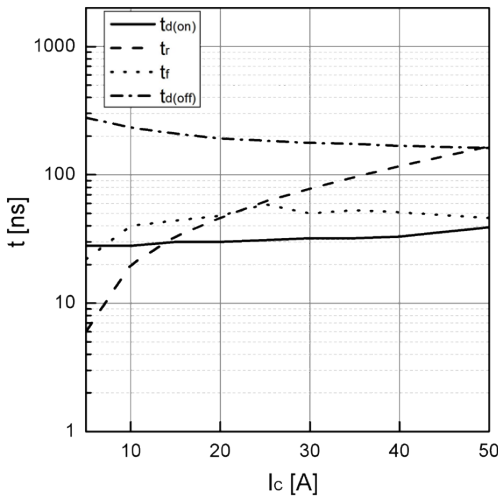


Fig 9. Typical switching time as a function of I_C

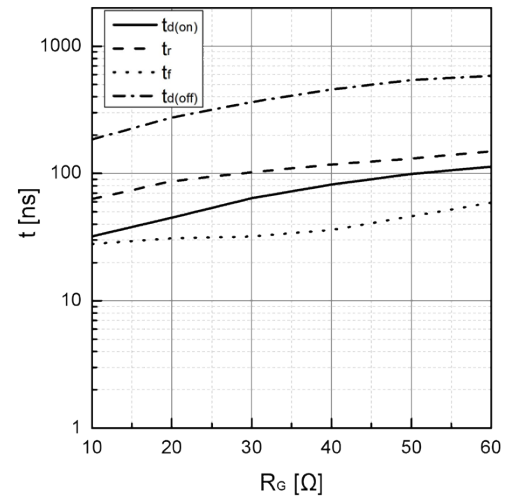


Fig 10. Typical switching times as a function of R_G

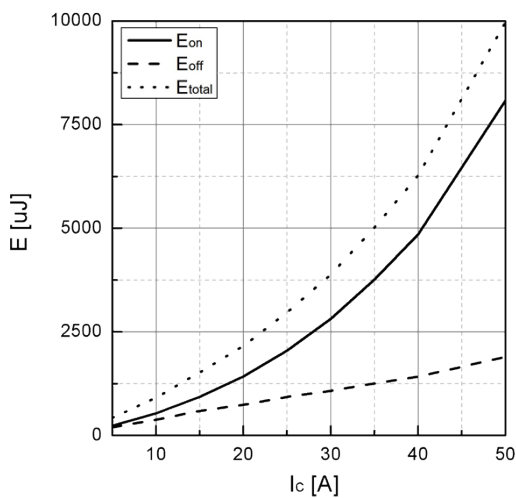


Fig 11. Typical switching energy losses as a function of I_C

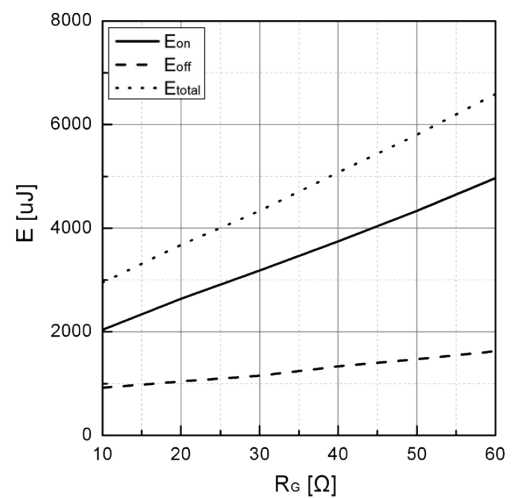


Fig 12. Typical switching energy losses as a function of R_G

Typical performance characteristics

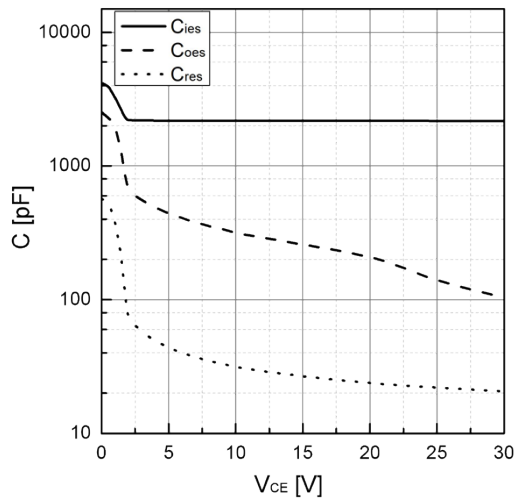


Fig 13. Typical capacitance as a function of V_{CE}
($f=1\text{MHz}$, $V_{GE}=0\text{V}$)

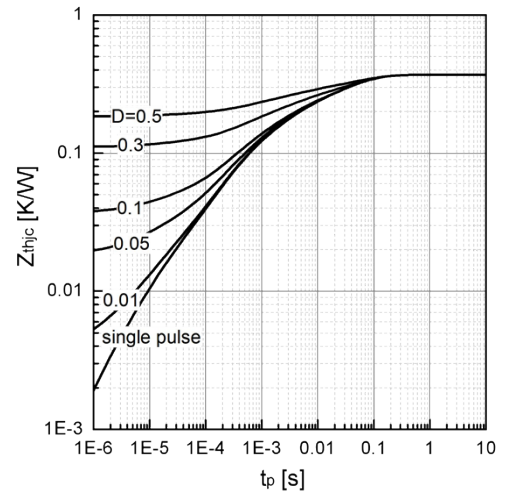


Fig 14. Transient thermal impedance of IGBT